

# Jerzy Kanicki

## List of Publications by Citations

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273  
papers

6,396  
citations

44  
h-index

68  
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311  
ext. papers

6,881  
ext. citations

2.8  
avg, IF

5.61  
L-index

#	Paper	IF	Citations
273	Bias-stress-induced stretched-exponential time dependence of charge injection and trapping in amorphous thin-film transistors. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1286-1288	3.4	384
272	Thin-film organic polymer phototransistors. <i>IEEE Transactions on Electron Devices</i> , <b>2004</b> , 51, 877-885	2.9	231
271	Two-dimensional numerical simulation of radio frequency sputter amorphous InGaZnO thin-film transistors. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 084511	2.5	193
270	Electrically active point defects in amorphous silicon nitride: An illumination and charge injection study. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 3558-3563	2.5	151
269	Density of States of a-InGaZnO From Temperature-Dependent Field-Effect Studies. <i>IEEE Transactions on Electron Devices</i> , <b>2009</b> , 56, 1177-1183	2.9	136
268	Performance of thin hydrogenated amorphous silicon thin-film transistors. <i>Journal of Applied Physics</i> , <b>1991</b> , 69, 2339-2345	2.5	119
267	High performance organic polymer light-emitting heterostructure devices. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 2265-2267	3.4	112
266	Gate dielectric and contact effects in hydrogenated amorphous silicon-silicon nitride thin-film transistors. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 3951-3957	2.5	109
265	Structural ordering and enhanced carrier mobility in organic polymer thin film transistors. <i>Synthetic Metals</i> , <b>2004</b> , 146, 181-185	3.6	96
264	High-efficiency organic polymer light-emitting heterostructure devices on flexible plastic substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 661-663	3.4	93
263	Electrical Instability of Hydrogenated Amorphous Silicon Thin-Film Transistors for Active-Matrix Liquid-Crystal Displays. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 4704-4710	1.4	91
262	Electrical Instability of RF Sputter Amorphous In-Ga-Zn-O Thin-Film Transistors. <i>Journal of Display Technology</i> , <b>2009</b> , 5, 452-461		89
261	Electron paramagnetic resonance investigation of charge trapping centers in amorphous silicon nitride films. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 4034-4046	2.5	89
260	Photofield-effect in amorphous In-Ga-Zn-O (a-IGZO) thin-film transistors. <i>Journal of Information Display</i> , <b>2008</b> , 9, 21-29	4.1	82
259	Paramagnetic Point Defects in Amorphous Silicon Dioxide and Amorphous Silicon Nitride Thin Films: II .. <i>Journal of the Electrochemical Society</i> , <b>1992</b> , 139, 880-889	3.9	82
258	Field-effect mobility of polycrystalline tetrabenzoporphyrin thin-film transistors. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 014503	2.5	79
257	Nature of the dominant deep trap in amorphous silicon nitride. <i>Physical Review B</i> , <b>1988</b> , 38, 8226-8229	3.3	79

256	Top-Gate Staggered Amorphous Silicon Thin-Film Transistors: Series Resistance and Nitride Thickness Effects. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 5914-5920	1.4	76
255	Improved a-Si:H TFT pixel electrode circuits for active-matrix organic light emitting displays. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 1322-1325	2.9	75
254	Current-source a-Si:H thin-film transistor circuit for active-matrix organic light-emitting displays. <i>IEEE Electron Device Letters</i> , <b>2000</b> , 21, 590-592	4.4	73
253	Organic polymer thin-film transistor photosensors. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2004</b> , 10, 840-848	3.8	72
252	Structural identification of the silicon and nitrogen dangling-bond centers in amorphous silicon nitride. <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 346-354	2.5	71
251	Ultraviolet light induced changes in polyimide liquid-crystal alignment films. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 5028-5034	2.5	67
250	Bias stress-induced instabilities in amorphous silicon nitride/hydrogenated amorphous silicon structures: Is the barrier-induced defect creation model correct?. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1197-1199	3.4	66
249	Influence of the Amorphous Silicon Thickness on Top Gate Thin-Film Transistor Electrical Performances. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 530-537	1.4	65
248	Electrical Properties and Stability of Dual-Gate Coplanar Homojunction DC Sputtered Amorphous Indium Gallium Zinc Oxide Thin-Film Transistors and Its Application to AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 4344-4353	2.9	60
247	Low frequency noise in long channel amorphous InGaZnO thin film transistors. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 074518	2.5	60
246	Si and N dangling bond creation in silicon nitride thin films. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 2685-2687	3.4	59
245	Solution-processed nickel tetrabenzoporphyrin thin-film transistors. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 034502	2.5	58
244	The nature of the dominant deep trap in amorphous silicon nitride films: Evidence for a negative correlation energy. <i>Applied Surface Science</i> , <b>1989</b> , 39, 392-405	6.7	57
243	Stable photoinduced paramagnetic defects in hydrogenated amorphous silicon nitride. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 608-610	3.4	55
242	High-resolution organic polymer light-emitting pixels fabricated by imprinting technique. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2002</b> , 20, 2877		52
241	Electron-spin-resonance study of defects in plasma-enhanced chemical vapor deposited silicon nitride. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 445-447	3.4	52
240	Solution-processed polycrystalline copper tetrabenzoporphyrin thin-film transistors. <i>Synthetic Metals</i> , <b>2007</b> , 157, 190-197	3.6	51
239	Evidence for a negative electron-electron correlation energy in the dominant deep trapping center in silicon nitride films. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1359-1361	3.4	51

238	Microscopic origin of the light-induced defects in hydrogenated nitrogen-rich amorphous silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , <b>1991</b> , 137-138, 291-294	3.9	51
237	Electrically neutral nitrogen dangling-bond defects in amorphous hydrogenated silicon nitride thin films. <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 2220-2225	2.5	50
236	Far UV pulsed laser melting of silicon. <i>Applied Physics Letters</i> , <b>1985</b> , 46, 547-549	3.4	50
235	Synthesis and Characterization of Conjugated, n-Dopable, Bithiazole-Containing Polymers. <i>Chemistry of Materials</i> , <b>1998</b> , 10, 1713-1719	9.6	48
234	P-13: Photosensitivity of Amorphous IGZO TFTs for Active-Matrix Flat-Panel Displays. <i>Digest of Technical Papers SID International Symposium</i> , <b>2008</b> , 39, 1215	0.5	46
233	Four-Thin Film Transistor Pixel Electrode Circuits for Active-Matrix Organic Light-Emitting Displays. <i>Japanese Journal of Applied Physics</i> , <b>2001</b> , 40, 1199-1208	1.4	46
232	Contact resistance to undoped and phosphorus-doped hydrogenated amorphous silicon films. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 1943-1945	3.4	46
231	High-fidelity electronic display of digital radiographs. <i>Radiographics</i> , <b>1999</b> , 19, 1653-69	5.4	45
230	Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 154505	2.5	44
229	Thermal annealing of light-induced metastable defects in hydrogenated amorphous silicon nitride. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 1723-1725	3.4	44
228	Observation of multiple silicon dangling bond configurations in silicon nitride. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 1043-1045	3.4	44
227	Energy level of the nitrogen dangling bond in amorphous silicon nitride. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 1699-1701	3.4	42
226	Field-Effect Mobility of Organic Polymer Thin-Film Transistors. <i>Chemistry of Materials</i> , <b>2004</b> , 16, 4699-4704	9.6	41
225	Stability of electrical properties of nitrogen-rich, silicon-rich, and stoichiometric silicon nitride films. <i>Journal of Applied Physics</i> , <b>1989</b> , 66, 2765-2767	2.5	41
224	Photobleaching of light-induced paramagnetic defects in amorphous silicon nitride films. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1995-1997	3.4	41
223	Amorphous InGaZnO Dual-Gate TFTs: Current-Voltage Characteristics and Electrical Stress Instabilities. <i>IEEE Transactions on Electron Devices</i> , <b>2012</b> , 59, 1928-1935	2.9	40
222	Investigation of the light-induced effects in nitrogen-rich silicon nitride films. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1112-1114	3.4	40
221	Patterning of transparent conducting oxide thin films by wet etching for a-Si:H TFT-LCDs. <i>Journal of Electronic Materials</i> , <b>1996</b> , 25, 1806-1817	1.9	39

220	Two-Dimensional Numerical Simulation of Solid-Phase-Crystallized Polysilicon Thin-Film Transistor Characteristics. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 2251-2255	1.4	37
219	Nature of the Si and N dangling bonds in silicon nitride. <i>Journal of Non-Crystalline Solids</i> , <b>1995</b> , 187, 297-300	3.0	37
218	Amorphous In-Ga-Zn-O thin-film transistor active pixel sensor x-ray imager for digital breast tomosynthesis. <i>Medical Physics</i> , <b>2014</b> , 41, 091902	4.4	36
217	Large area CMOS active pixel sensor x-ray imager for digital breast tomosynthesis: Analysis, modeling, and characterization. <i>Medical Physics</i> , <b>2015</b> , 42, 6294-308	4.4	36
216	High field-effect-mobility a-Si:H TFT based on high deposition-rate PECVD materials. <i>IEEE Electron Device Letters</i> , <b>1996</b> , 17, 437-439	4.4	36
215	DC sputtered amorphous In <sub>5</sub> N <sub>5</sub> O thin-film transistors: Electrical properties and stability. <i>Solid-State Electronics</i> , <b>2016</b> , 116, 22-29	1.7	35
214	Gated-four-probe a-Si:H TFT structure: a new technique to measure the intrinsic performance of a-Si:H TFT. <i>IEEE Electron Device Letters</i> , <b>1997</b> , 18, 340-342	4.4	35
213	Absolute photoluminescence quantum efficiency measurement of light-emitting thin films. <i>Review of Scientific Instruments</i> , <b>2007</b> , 78, 096101	1.7	34
212	Polycrystalline tetrabenzoporphyrin organic field-effect transistors with nanostructured channels. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 233107	3.4	34
211	Stretched exponential illumination time dependence of positive charge and spin generation in amorphous silicon nitride. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 698-700	3.4	34
210	Metal - Polyacetylene Schottky Barrier Diodes. <i>Molecular Crystals and Liquid Crystals</i> , <b>1984</b> , 105, 203-217	0.5	34
209	Transparent flexible plastic substrates for organic light-emitting devices. <i>Journal of Electronic Materials</i> , <b>2004</b> , 33, 312-320	1.9	32
208	Angular dependence of the luminance and contrast in medical monochrome liquid crystal displays. <i>Medical Physics</i> , <b>2003</b> , 30, 2602-13	4.4	32
207	ITO surface ball formation induced by atomic hydrogen in PECVD and HW-CVD tools. <i>Thin Solid Films</i> , <b>1997</b> , 304, 123-129	2.2	31
206	A novel current-scaling a-Si:H TFTs pixel electrode circuit for AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1123-1131	2.9	28
205	Monte Carlo analysis of the spectral photon emission and extraction efficiency of organic light-emitting devices. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 1827-1830	2.5	26
204	Charge trapping centers in N-rich silicon nitride thin films. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 216-218	3.4	26
203	Top illuminated organic photodetectors with dielectric/metal/dielectric transparent anode. <i>Organic Electronics</i> , <b>2015</b> , 20, 103-111	3.5	24

202	Creation and Properties of Nitrogen Dangling Bond Defects in Silicon Nitride Thin Films. <i>Journal of the Electrochemical Society</i> , <b>1996</b> , 143, 3685-3691	3.9	24
201	Electrical properties of staggered electrode, solution-processed, polycrystalline tetrabenzoporphyrin field-effect transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1497-1503	2.9	24
200	Properties of High Conductivity Phosphorous Doped Hydrogenated Microcrystalline Silicon and Application in Thin Film Transistor Technology. <i>Materials Research Society Symposia Proceedings</i> , <b>1989</b> , 149, 239		24
199	Asymmetric Electrical Properties of Corbino a-Si:H TFT and Concepts of Its Application to Flat Panel Displays. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 654-662	2.9	23
198	Temperature Dependent Characteristics of Hydrogenated Amorphous Silicon thin film Transistors. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 118, 267		23
197	50 $\mu\text{m}$ pixel pitch wafer-scale CMOS active pixel sensor x-ray detector for digital breast tomosynthesis. <i>Physics in Medicine and Biology</i> , <b>2015</b> , 60, 8977-9001	3.8	22
196	Oxygen flow effects on electrical properties, stability, and density of states of amorphous $\text{InGaZnO}$ thin-film transistors. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 121101	1.4	22
195	Investigation of intrinsic channel characteristics of hydrogenated amorphous silicon thin-film transistors by gated-four-probe structure. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2874-2876	3.4	22
194	Planarized copper gate hydrogenated amorphous-silicon thin-film transistors for AM-LCDs. <i>IEEE Electron Device Letters</i> , <b>1999</b> , 20, 129-131	4.4	22
193	Photodarkening and bleaching in amorphous silicon nitride. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1378-1380	3.4	22
192	Crystalline $\text{InGaZnO}$ Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 091102	1.4	22
191	Short channel amorphous $\text{InGaZnO}$ thin-film transistor arrays for ultra-high definition active matrix liquid crystal displays: Electrical properties and stability. <i>Solid-State Electronics</i> , <b>2015</b> , 111, 67-75	1.7	21
190	Amorphous $\text{InGaZnO}$ Thin Film Transistor Current-Scaling Pixel Electrode Circuit for Active-Matrix Organic Light-Emitting Displays. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 03B025	1.4	20
189	A maskless laser-write lithography processing of thin-film transistors on a hemispherical surface. <i>Microelectronic Engineering</i> , <b>2010</b> , 87, 83-87	2.5	20
188	Ultraviolet-light Induced Liquid-Crystal Alignment on Polyimide Films. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 5996-6004	1.4	20
187	Electrical Instability of Double-Gate a-IGZO TFTs With Metal Source/Drain Recessed Electrodes. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 1109-1115	2.9	19
186	Analyte selective response in solution-deposited tetrabenzoporphyrin thin-film field-effect transistor sensors. <i>Sensors and Actuators B: Chemical</i> , <b>2011</b> , 158, 333-339	8.5	19
185	Tuning Optical and Electronic Properties of Bithiazole Containing Polymers by N-Methylation. <i>Macromolecules</i> , <b>1999</b> , 32, 2484-2489	5.5	19

184	Role of Hydrogen in Silicon Nitride Films Prepared by Various Deposition Techniques. <i>Materials Research Society Symposia Proceedings</i> , <b>1988</b> , 118, 671		19
183	Dynamic Response of a-InGaZnO and Amorphous Silicon Thin-Film Transistors for Ultra-High Definition Active-Matrix Liquid Crystal Displays. <i>Journal of Display Technology</i> , <b>2015</b> , 11, 471-479		18
182	Atomic Hydrogen Effects on the Optical and Electrical Properties of Transparent Conducting Oxides For a-Si:H TFT-LCDs. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 424, 347		18
181	Asymmetric electrical properties of fork a-Si:H thin-film transistor and its application to flat panel displays. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 124522	2.5	17
180	Advanced Amorphous Silicon Thin-Film Transistors for AM-OLEDs: Electrical Performance and Stability. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 1621-1629	2.9	17
179	Defects in amorphous hydrogenated silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , <b>1993</b> , 164-166, 1055-1060	3.9	17
178	Spatial charge distribution in the plasma-enhanced chemical vapor deposited nitrogen-rich silicon nitride. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 733-735	3.4	17
177	Bilayer Interdiffused Heterojunction Organic Photodiodes Fabricated by Double Transfer Stamping. <i>Advanced Optical Materials</i> , <b>2017</b> , 5, 1600784	8.1	16
176	An a-InGaZnO TFT Pixel Circuit Compensating Threshold Voltage and Mobility Variations in AMOLEDs. <i>Journal of Display Technology</i> , <b>2014</b> , 10, 402-406		16
175	Properties of Electrodeposited WO <sub>3</sub> Thin Films. <i>Molecular Crystals and Liquid Crystals</i> , <b>2014</b> , 604, 71-83	0.5	15
174	Opto-electronic properties of poly (fluorene) co-polymer red light-emitting devices on flexible plastic substrate. <i>IEEE Transactions on Electron Devices</i> , <b>2004</b> , 51, 1562-1569	2.9	15
173	Interference fringe-free transmission spectroscopy of amorphous thin films. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 5764-5771	2.5	15
172	Direct observation of the silicon nitride on amorphous silicon interface states. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 940-942	3.4	15
171	Solution-processed zinc tetrabenzoporphyrin thin-films and transistors. <i>Thin Solid Films</i> , <b>2012</b> , 520, 4031-4035	2.9	14
170	Characterization and stability of light-emitting diodes based on poly(bithiazole)'s. <i>IEEE Transactions on Electron Devices</i> , <b>1997</b> , 44, 1282-1288	2.9	14
169	Current-Scaling a-Si:H TFT Pixel-Electrode Circuit for AM-OLEDs: Electrical Properties and Stability. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 2403-2410	2.9	14
168	Light output measurements of the organic light-emitting devices. <i>Review of Scientific Instruments</i> , <b>2000</b> , 71, 2104-2107	1.7	14
167	Observation of incident angle dependent phonon absorption in hydrogenated amorphous silicon nitride thin films. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 3866-3868	3.4	14

166	Paramagnetic point defects in silicon nitride and silicon oxynitride thin films on silicon. <i>Colloids and Surfaces A: Physicochemical and Engineering Aspects</i> , <b>1996</b> , 115, 311-317	5.1	14
165	Photovoltaic properties of the poly-2-vinylpyridine iodine complex/BnO <sub>2</sub> system. <i>Journal of Applied Polymer Science</i> , <b>1982</b> , 27, 1-9	2.9	14
164	Electrochromic device with Prussian blue and HPC-based electrolyte. <i>Electrochimica Acta</i> , <b>2015</b> , 182, 878-883	6.7	13
163	P-11: DC/AC Electrical Instability of R.F. Sputter Amorphous In-Ga-Zn-O TFTs. <i>Digest of Technical Papers SID International Symposium</i> , <b>2009</b> , 40, 1117	0.5	13
162	Hexagonal a-Si:H TFTs: A New Advanced Technology for Flat-Panel Displays. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 329-336	2.9	13
161	Advanced Multilayer Amorphous Silicon Thin-Film Transistor Structure: Film Thickness Effect on Its Electrical Performance and Contact Resistance. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 3362-3367 <sup>1.4</sup>	1.4	13
160	Electrical characteristics of new LDD poly-Si TFT structure tolerant to process misalignment. <i>IEEE Electron Device Letters</i> , <b>1999</b> , 20, 335-337	4.4	13
159	Some electrical properties of amorphous silicon/amorphous silicon nitride interfaces: Top nitride and bottom nitride configurations in MNS and TFT devices. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 5022-5032 <sup>2.5</sup>	2.5	13
158	Investigations on the quality of polysilicon film-gate dielectric interface in polysilicon thin film transistors. <i>Thin Solid Films</i> , <b>1992</b> , 216, 137-141	2.2	13
157	Two-Dimensional Numerical Simulation of Bottom-Gate and Dual-Gate Amorphous In-Ga-Zn-O MESFETs. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 75-77	4.4	12
156	High Efficiency Cu(In,Ga)Se <sub>2</sub> Flexible Solar Cells Fabricated by Roll-to-Roll Metallic Precursor Co-sputtering Method. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 092302	1.4	12
155	Dynamic Response of Normal and Corbino a-Si:H TFTs for AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 2338-2347	2.9	12
154	Novel Current-Scaling Current-Mirror Hydrogenated Amorphous Silicon Thin-Film Transistor Pixel Electrode Circuit with Cascade Capacitor for Active-Matrix Organic Light-Emitting Devices. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 1343-1349	1.4	12
153	Poly(fluorene-oxadiazole) copolymer-based light-emitting devices on a plastic substrate. <i>Synthetic Metals</i> , <b>2005</b> , 155, 1-10	3.6	12
152	Structural ordering in F8T2 polyfluorene thin film transistors <b>2003</b> , 5217, 35		12
151	Accurate small-spot luminance measurements. <i>Displays</i> , <b>2002</b> , 23, 177-182	3.4	12
150	Optoelectrical properties of four amorphous silicon thin-film transistors 200 dpi active-matrix organic polymer light-emitting display. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3233-3235	3.4	12
149	Methanofullerene-coated tetrabenzoporphyrin organic field-effect transistors. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 173506	3.4	12



148	Ultraviolet light induced annihilation of silicon dangling bonds in hydrogenated amorphous silicon nitride films. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 5730-5735	2.5	12
147	. <i>IEEE Electron Device Letters</i> , <b>1989</b> , 10, 277-279	4.4	12
146	Electrical conductivity and infrared absorption of trans- polyacetylene in the presence of iodine. <i>Journal of the Chemical Society, Faraday Transactions 2</i> , <b>1981</b> , 77, 2157-2168		12
145	Half-Corbino short-channel amorphous InGaZnO thin-film transistors with a-SiO <sub>x</sub> or a-SiO <sub>x</sub> /a-SiN <sub>x</sub> passivation layers. <i>Solid-State Electronics</i> , <b>2016</b> , 120, 25-31	1.7	12
144	Novel Top-Anode OLED/a-IGZO TFTs Pixel Circuit for 8K4K AM-OLEDs. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 436-444	2.9	12
143	Surface potential study of amorphous InGaZnO thin film transistors. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 114508	2.5	11
142	Crystalline InGaZnO Density of States and Energy Band Structure Calculation Using Density Function Theory. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 091102	1.4	11
141	Influence of gate dielectrics on electrical properties of F8T2 polyfluorene thin film transistors <b>2003</b>		11
140	Integrating sphere charge coupled device-based measurement method for organic light-emitting devices. <i>Review of Scientific Instruments</i> , <b>2003</b> , 74, 3572-3575	1.7	11
139	Selective deposition of polycrystalline silicon thin films at low temperature by hot-wire chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 2681-2683	3.4	11
138	Enhanced electro-optic effect in amorphous hydrogenated silicon based waveguides. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 1664-1666	3.4	11
137	Light-induced effects in hydrogenated amorphous nitrogen-rich silicon nitride films. <i>Journal of Non-Crystalline Solids</i> , <b>1989</b> , 114, 612-614	3.9	11
136	Electrical and photovoltaic properties of trans-polyacetylene. <i>Journal Physics D: Applied Physics</i> , <b>1984</b> , 17, 805-817	3	11
135	. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 4802-4810	2.9	11
134	Schottky-contact gated-four-probe a-Si:H TFT structure: a new structure to investigate the electrical instability of a-Si:H TFT. <i>IEEE Electron Device Letters</i> , <b>1998</b> , 19, 382-384	4.4	10
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132	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2004</b> , 10, 16-25	3.8	10
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